

isc Silicon NPN RF Transistor

2SC2759

DESCRIPTION

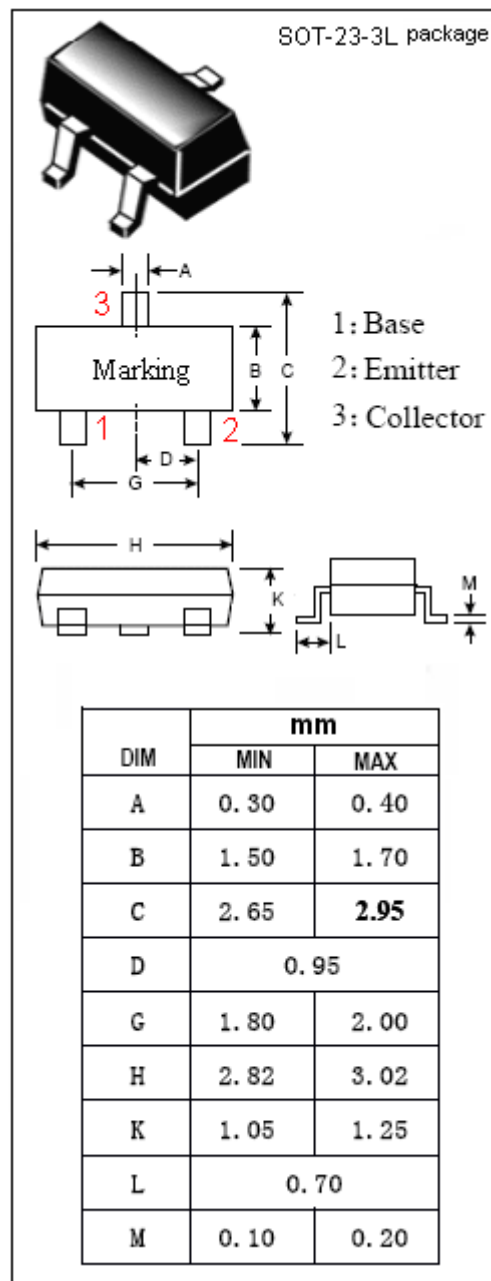
- Low Noise
 - High Conversion Gain
- $G_{cb} = 12.5\text{dB TYP.}$ @ $I_E = -5\text{mA}$, $V_{CB} = 10\text{V}$

APPLICATIONS

- Designed for use in VHF RF amplifier, local oscillator, mixer.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	14	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current-Continuous	50	mA
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	0.15	W
T_J	Junction Temperature	125	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~125	$^\circ\text{C}$



isc Silicon NPN RF Transistor**2SC2759****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I _{CBO}	Collector Cutoff Current	V _{CB} = 15V; I _E = 0			0.1	μ A
h _{FE}	DC Current Gain	I _C = 5mA ; V _{CE} = 10V	40		180	
f _T	Current-Gain—Bandwidth Product	I _C = 5mA ; V _{CE} = 10V	1.5	2.0		GHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f= 1.0MHz		1.0	1.3	pF
G _{cb}	Conversion Gain	I _E = -5mA ; V _{CB} = 10V; f= 900MHz; f _{OSC} = 935MHz, 115 dB μ V	10	12.5		dB

◆ h_{FE} Classification

Marking	U21	U22	U23
h _{FE}	40-80	60-120	90-180